

CD4000B, CD4001B, CD4002B, CD4025B Types

CMOS NOR Gates

High-Voltage Types (20-Volt Rating)

Dual 3 Input

plus Inverter – CD4000B

Quad 2 Input – CD4001B

Dual 4 Input – CD4002B

Triple 3 Input – CD4025B

RCA-CD4000B, CD4001B, CD4002B, and CD4025B NOR gates provide the system designer with direct implementation of the NOR function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4000B, CD4001B, CD4002B, and CD4025B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

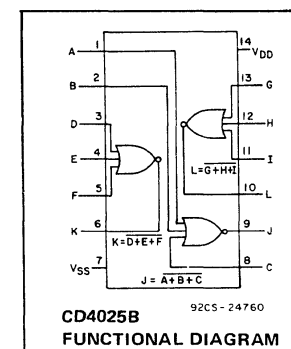
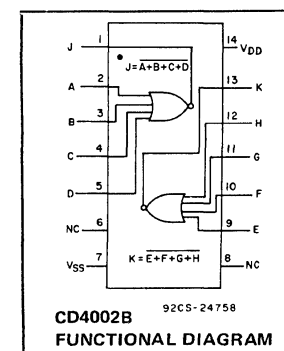
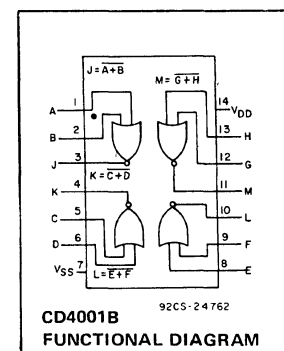
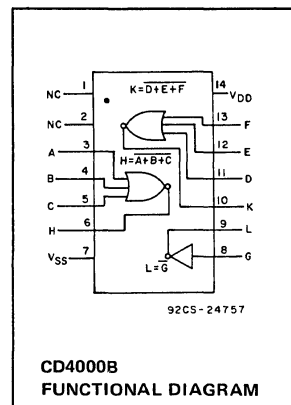
- Propagation delay time = 60 ns (typ.) at $C_L = 50$ pF, $V_{DD} = 10$ V
- Buffered inputs and outputs
- Standardized symmetrical output characteristics
- 100% tested for maximum quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):

1 V at $V_{DD} = 5$ V

2 V at $V_{DD} = 10$ V

2.5 V at $V_{DD} = 15$ V

- Meets all requirements of JEDEC Tentative Standard No.13A, "Standard Specifications for Description of "B" Series CMOS Devices"



STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	Values at −55, +25, +125 Apply to D,F,K,H Packages Values at −40, +25, +85 Apply to E Package							
				−55	−40	+85	+125	+25			
Quiescent Device Current, I _{DD} Max.	—	0,5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0,10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0,15	15	1	1	30	30	—	0.01	1	
	—	0,20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	—	mA
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	—	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	—	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	0.5,4.5	—	5	1.5				—	—	1.5	V
	1,9	—	10	3				—	—	3	
	1.5,13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	0.5	—	5	3.5				3.5	—	—	V
	1	—	10	7				7	—	—	
	1.5	—	15	11				11	—	—	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ^{−5}	±0.1	μA

CD4000B, CD4001B, CD4002B, CD4025B Types

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

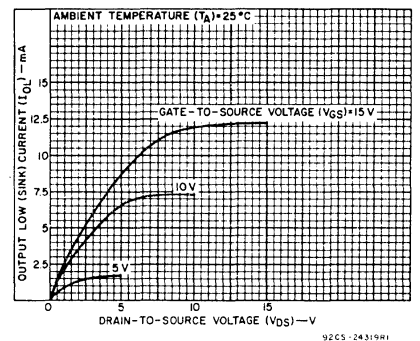
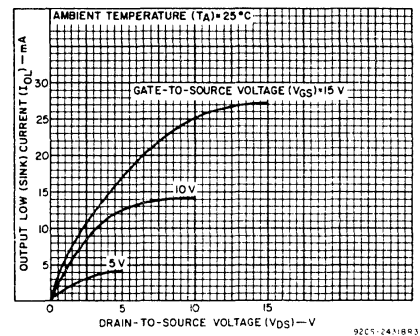
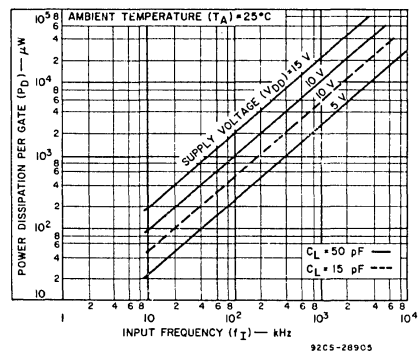
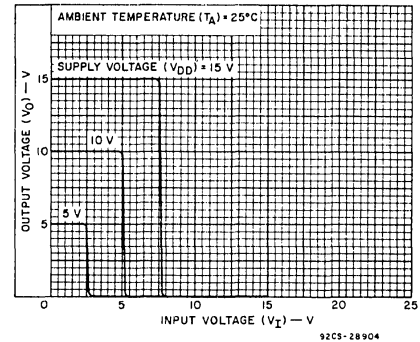
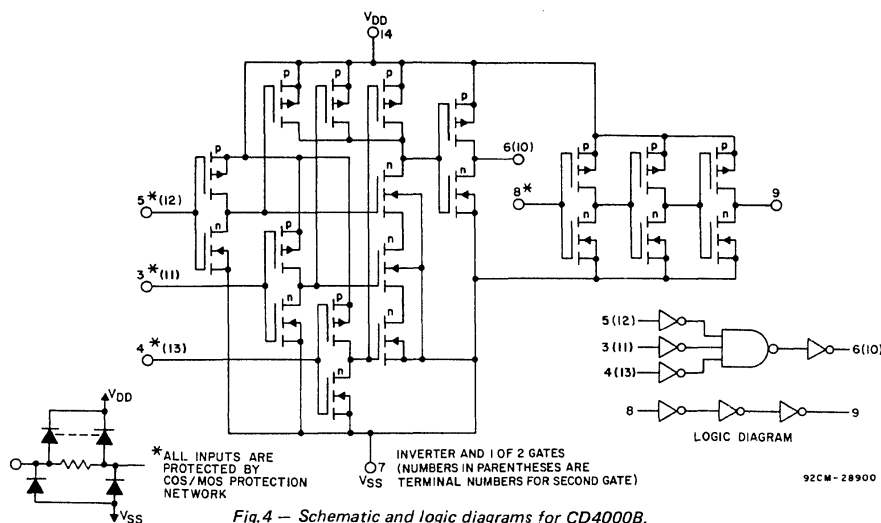
MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})	(Voltages referenced to V_{SS} Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS		-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT		± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):		
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)		500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$	to 200 mW
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K)		500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ\text{C}$	to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR		
FOR T_A - FULL PACKAGE-TEMPERATURE RANGE (All Package Types)		100 mW
OPERATING-TEMPERATURE RANGE (T_A):		
PACKAGE TYPES D, F, K, H		-55 to $+125^\circ\text{C}$
PACKAGE TYPE E		-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})		-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):		
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79 mm) from case for 10 s max.		$+265^\circ\text{C}$

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20$ ns, $C_L = 50$ pF, $R_L = 200k\Omega$

CHARACTERISTIC	TEST CONDITIONS	ALL TYPES LIMITS		UNITS	
		V _{DD} VOLTS	TYP.		MAX.
Propagation Delay Time, t _{PHL} , t _{PLH}		5 10 15	125 60 45	250 120 90	ns
Transition Time, t _{THL} , t _{TLH}		5 10 15	100 50 40	200 100 80	ns
Input Capacitance, C _{IN}	Any Input		5	7.5	pF



CD4000B, CD4001B, CD4002B, CD4025B Types

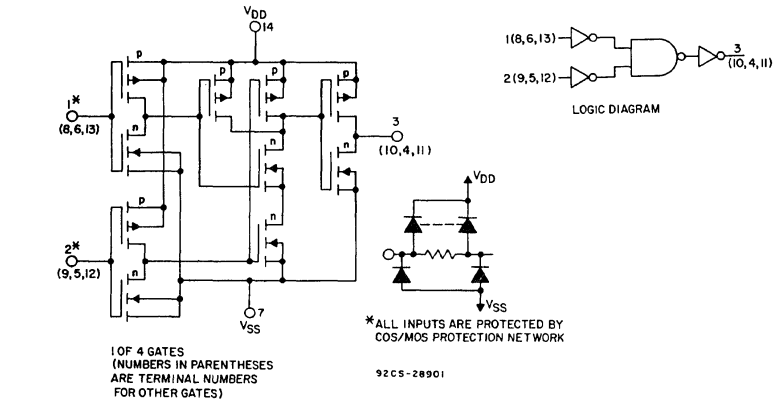


Fig.6 — Schematic and logic diagrams for CD4001B.

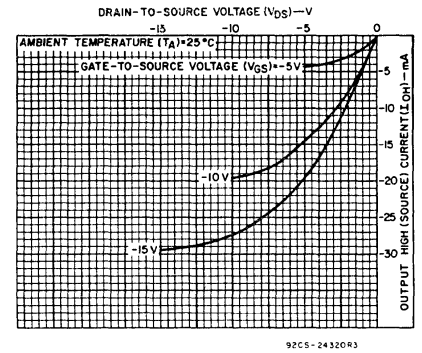


Fig.9 — Typical output high (source) current characteristics.

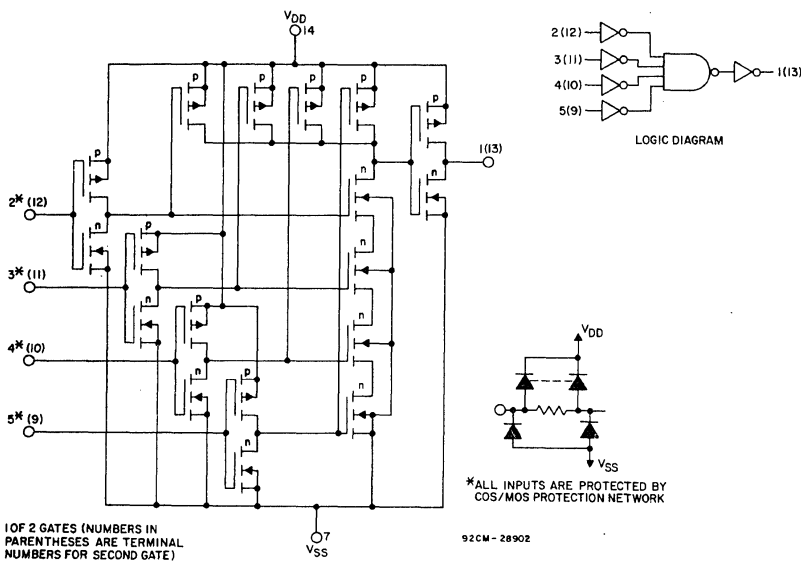


Fig.7 — Schematic and logic diagrams for CD4002B.

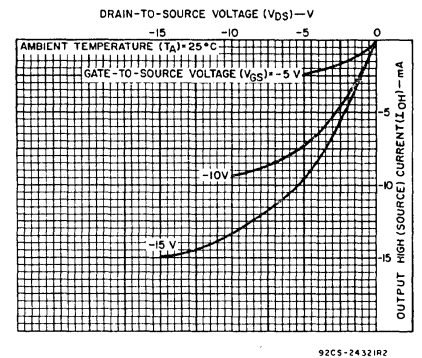


Fig.10 — Minimum output high (source) current characteristics.

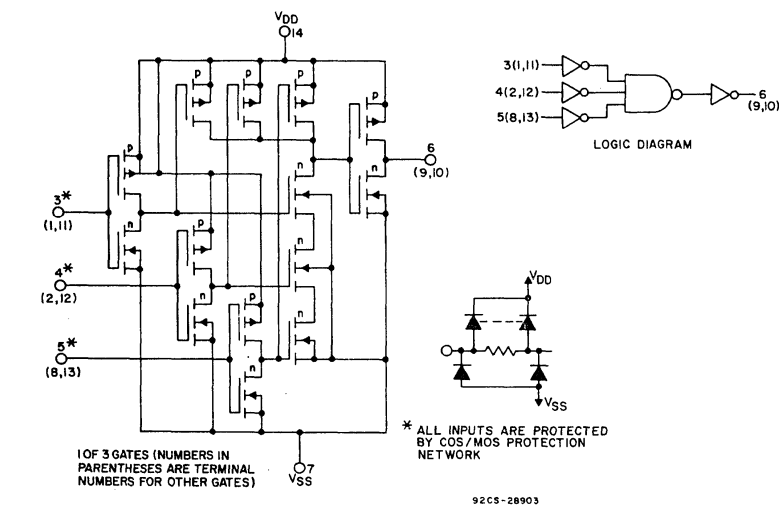


Fig.8 — Schematic and logic diagrams for CD4025B.

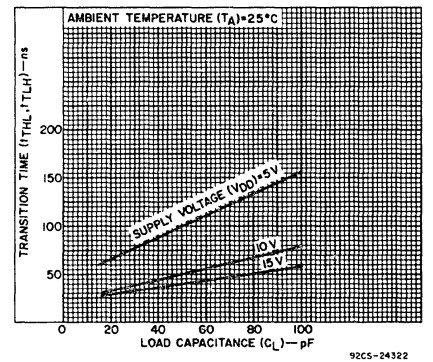


Fig.11 — Typical transition time vs. load capacitance.

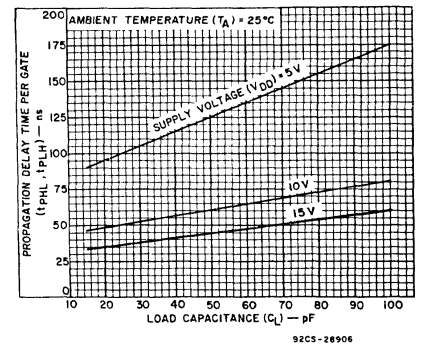


Fig.12 — Typical propagation delay time vs. load capacitance.

CD4000B, CD4001B, CD4002B, CD4025B Types

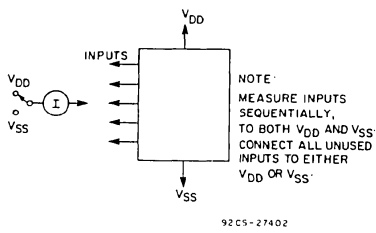


Fig. 13 - Input leakage current test circuit.

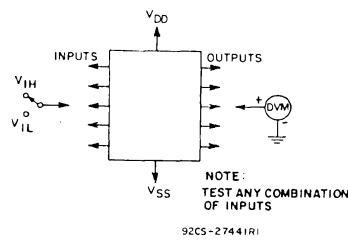


Fig. 14 - Input-voltage test circuit.

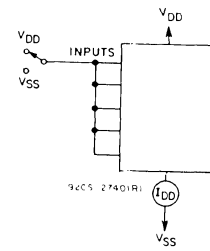
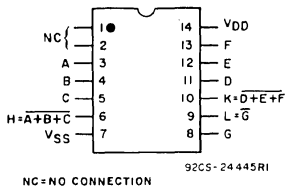
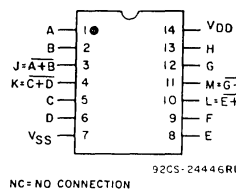


Fig. 15 - Quiescent-device current test circuit.

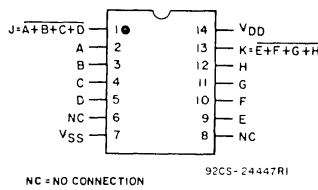
TERMINAL ASSIGNMENTS (TOP VIEW)



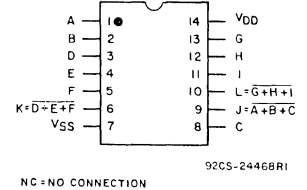
CD4000B



CD4001B

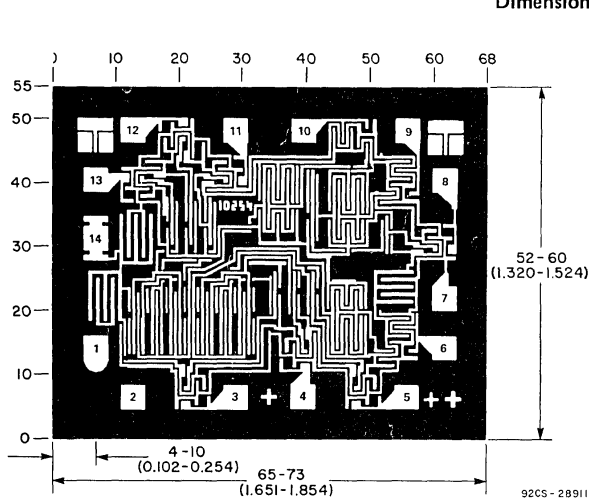


CD4002B

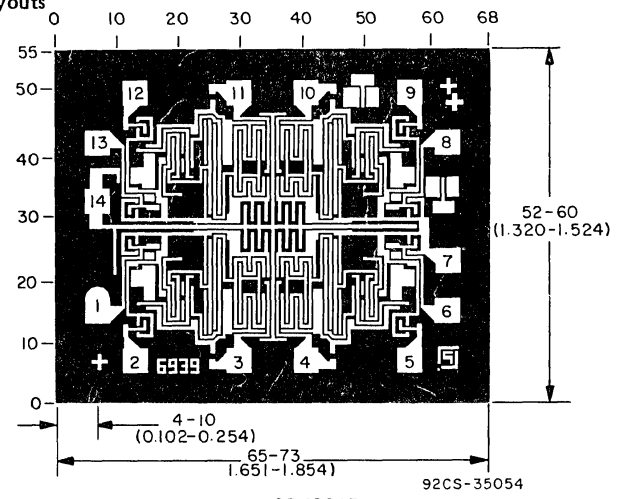


CD4025B

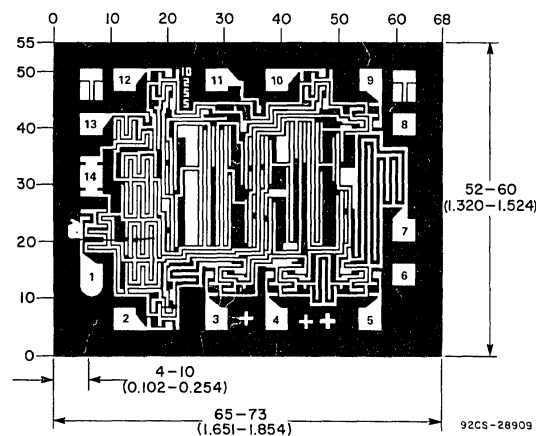
CHIP PHOTOGRAPHS Dimensions and Pad Layouts



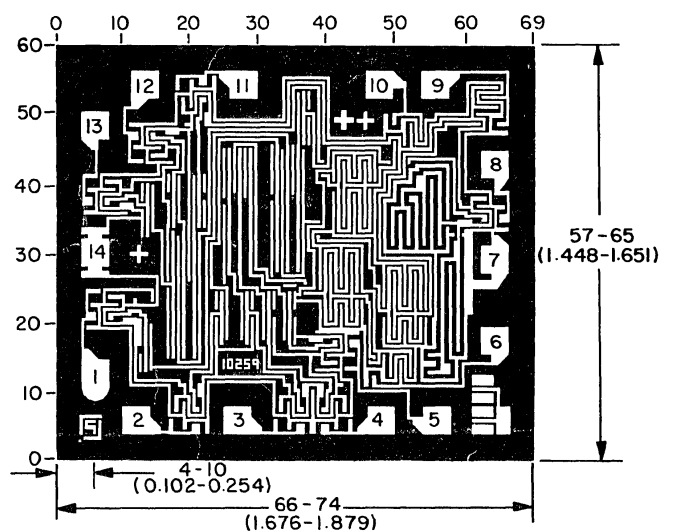
CD4000B



CD4001B



CD4002B



CD4025B